

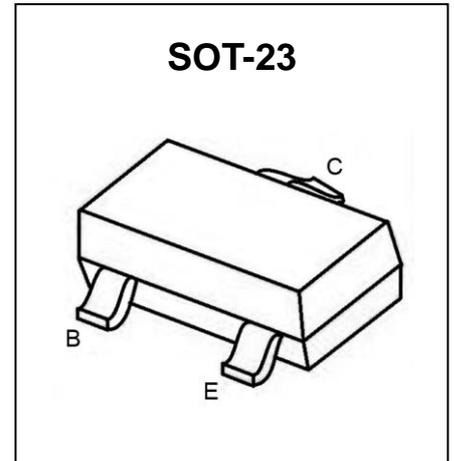
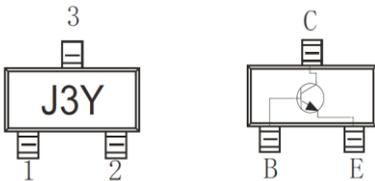


S8050 Transistor(NPN)

Feature

- Good current characters
- Small saturable voltage drop
- High Breakdown voltage

Marking:



Classification of h_{FE}:

Rank	L	H
Range	120-200	200-350

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

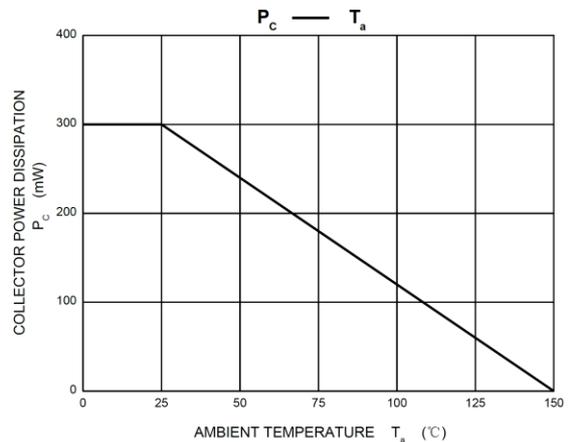
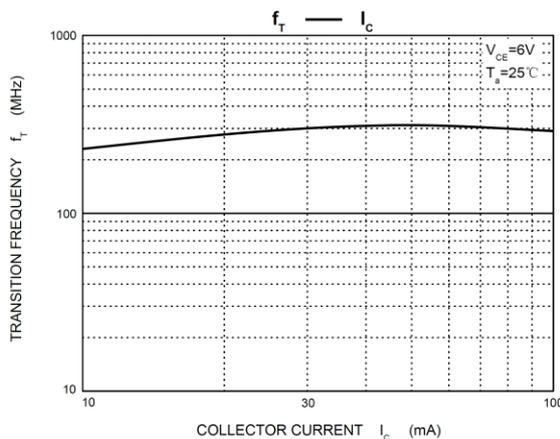
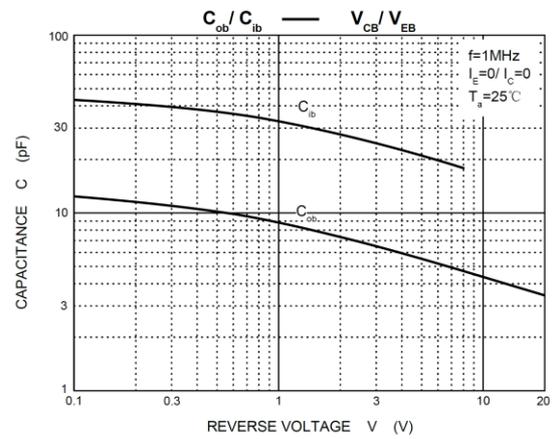
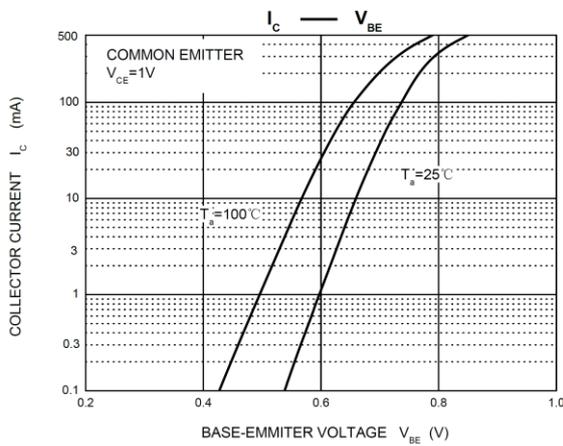
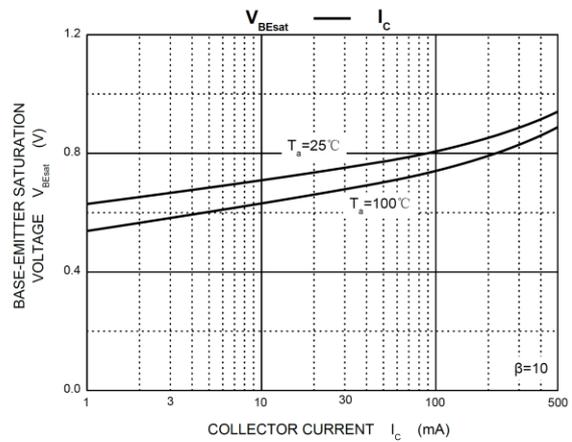
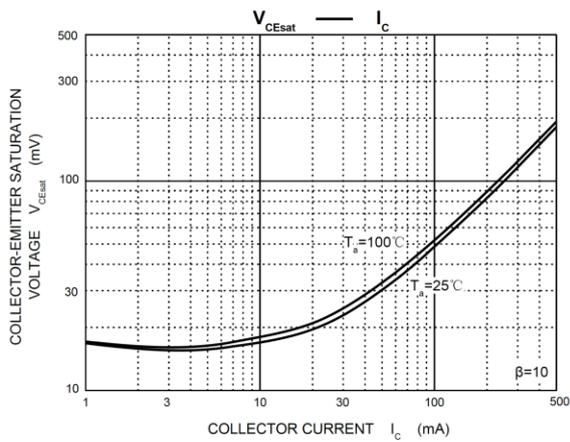
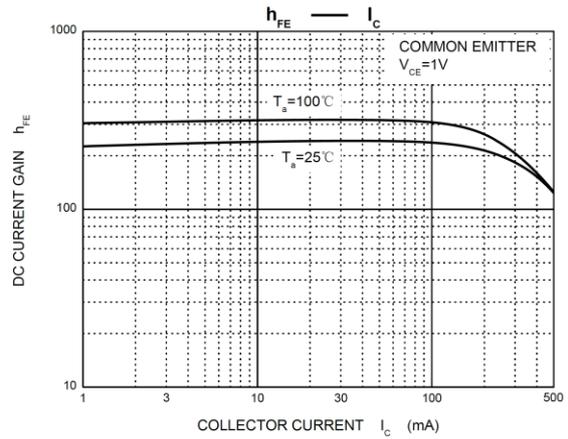
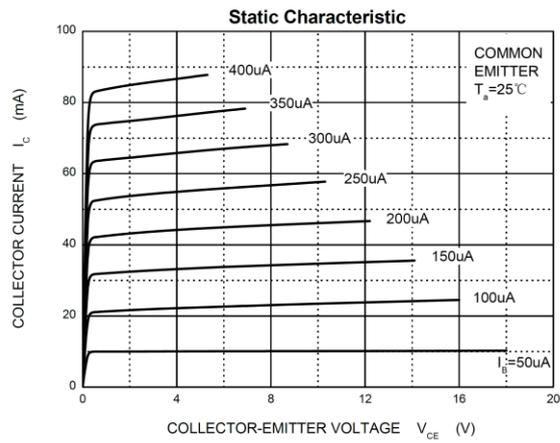
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CE0}	25	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current -Continuous	I _c	0.5	A
Power Dissipation	P _d	0.3	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

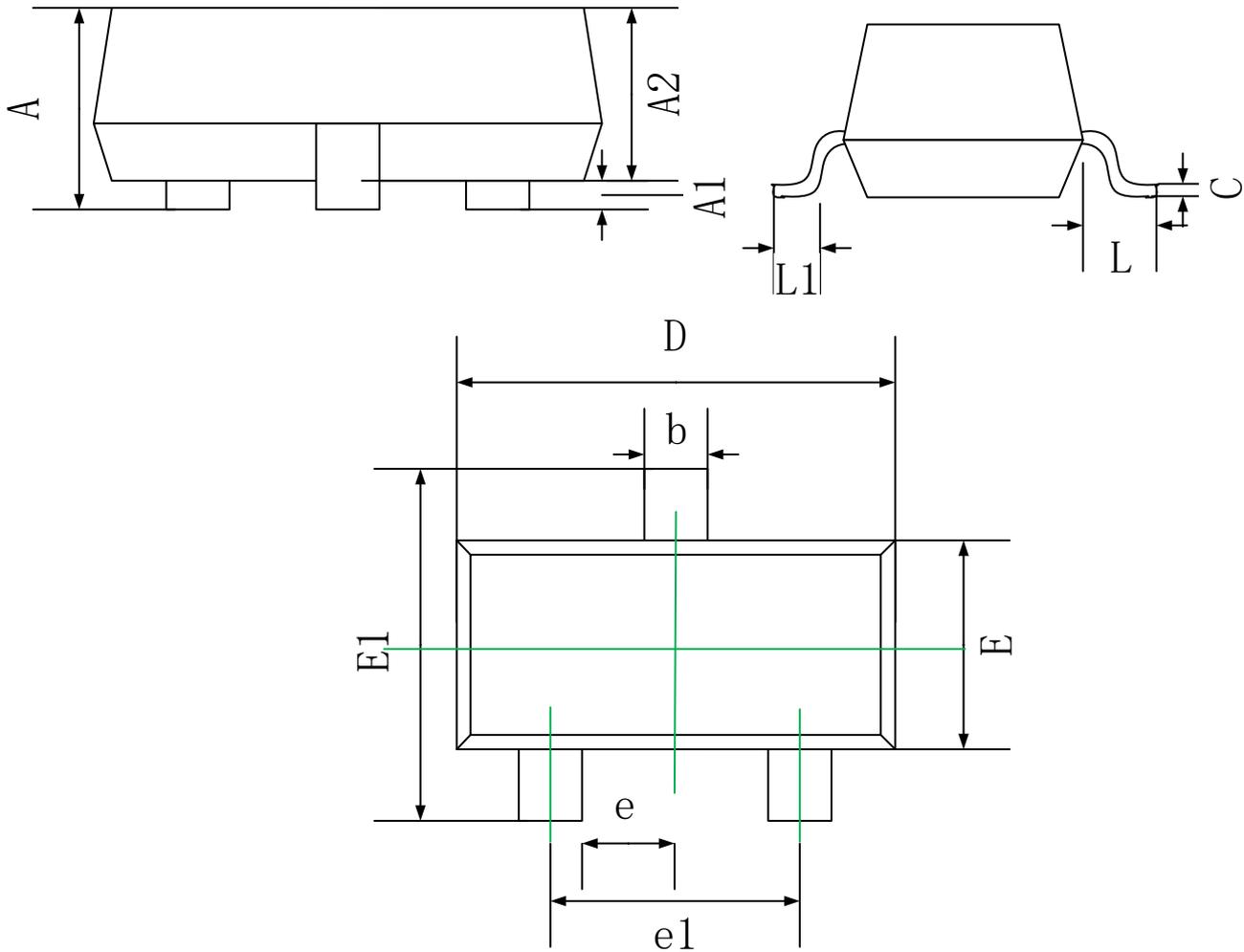
ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$		100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=20\text{V}, I_B=0$		100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC current gain	h_{FE}	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40		
		$V_{CE}=1\text{V}, I_C=1\text{mA}$	70		
		$V_{CE}=1\text{V}, I_C=50\text{mA}$	100	400	
		$V_{CE}=1\text{V}, I_C=100\text{mA}$	60		
		$V_{CE}=1\text{V}, I_C=500\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.5	V
		$I_C=500\text{mA}, I_B=50\text{mA}$		0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.1	V
		$I_C=500\text{mA}, I_B=50\text{mA}$		1.2	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=20\text{mA}, f=30\text{MHz}$	150		MHZ
Input Capacitance	C_{IB}	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$		4.0	pF
Output Capacitance	C_{OB}	$V_{EB}=0.5\text{V}, I_C=0, f=1\text{MHz}$		8.0	pF
Delay Time	t_d	$V_{CC}=3\text{V}, V_{BE}=-0.5\text{V}, I_C=10\text{mA}, I_B=1.0\text{mA}$		35	nS
Rise Time	t_r			35	nS
Storage Time	t_s			200	nS
Fall Time	t_f	$V_{CC}=3\text{V}, V_{BE}=-0.5\text{V}, I_{B1}=I_{B2}=1.0\text{mA}$		50	nS

*Pulse Test : Pulse width<300Us , Duty Cycle < 2.0%.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50